

Schottky barrier diode

RB876W

●Applications

High frequency detection

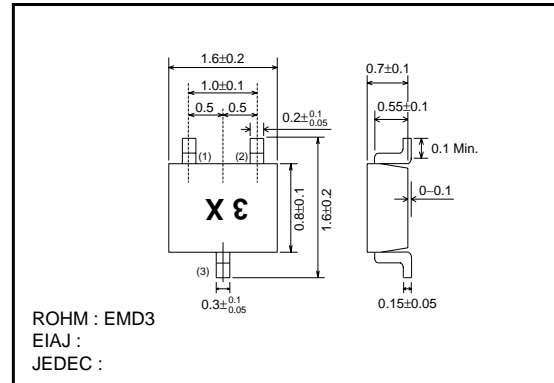
●Features

- 1) Ultra small mold type. (EMD3)
- 2) Low Ct and high detection efficiency.

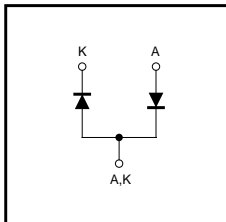
●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	5	V
Forward current (DC)	I_F	10	mA
Junction temperature	T_J	125	°C
Storage temperature	T_{stg}	-40~+125	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.35	V	$I_F=1.0\text{mA}$
Reverse current	I_R	-	-	120	μA	$V_R=5.0\text{V}$
Capacitance between terminal	C_T	-	0.53	0.80	pF	$V_R=1.0\text{V}$, $f=1.0\text{MHz}$

* Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

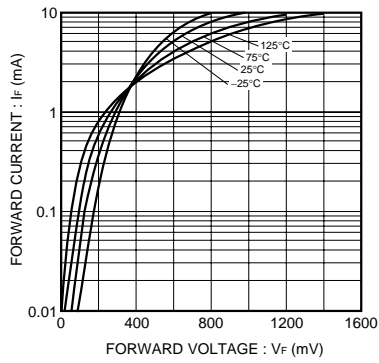


Fig.1 Forward characteristics

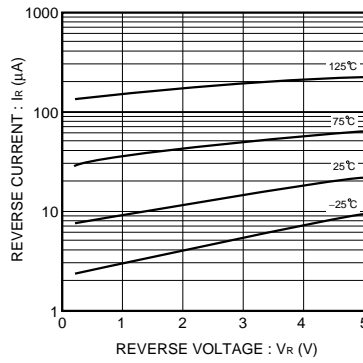


Fig.2 Reverse characteristics

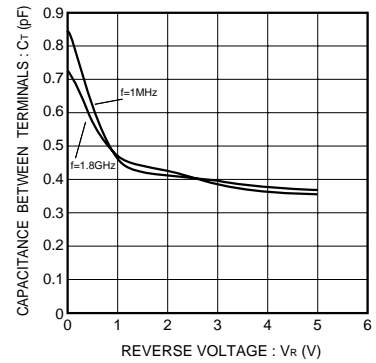


Fig.3 Capacitance between terminals characteristics